Nondestructive Memory Elements Based on Polymeric Langmuir-Blodgett Thin Films

T.J. REECE, S. DUCHARME, Department of Physics and Astronomy, Nebraska Center for Materials and Nanoscience, University of Nebraska at Lincoln — Ferroelectric field effect transistors (FeFETs) have attracted much attention recently because of their low power consumption and fast nondestructive readout. Among the ferroelectric thin films used in FET devices; the ferroelectric copolymer of polyvinylidene fluoride, PVDF ($C_2H_2F_2$), with trifluoroethylene, TrFE ($C_2HF_3$), has distinct advantages, including low dielectric constant, low processing temperature, low cost and compatibility with organic semiconductors. By employing the Langmuir-Blodgett technique, we are able to deposit films as thin as 1.8 nm. We discuss the characterization, modeling and fabrication of metal-ferroelectric-insulator-semiconductor (MFIS) structures incorporating these films.

1 This work is supported by the National Science Foundation.

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Date submitted: 02 Dec 2006 Electronic form version 1.4